High Quality Gate Dielectric/MoS2 Interfaces Probed by the Conductance Method

2018

Adithi Pandrahal Krishnaprasad Sharada

University of Central Florida
HIGH QUALITY GATE DIELECTRIC/MoS$_2$ INTERFACES PROBED BY THE CONDUCTANCE METHOD

by

ADITHI PANDRAHALLY KRISHNAPRASAD SHARADA

B.E. Visvesvaraya Technological University, 2015

A thesis submitted in partial fulfilment of the requirements
for the degree of Master of Science
in the Department of Electrical Engineering and Computer Science
in the College of Engineering and Computer Science
at the University of Central Florida

Orlando, Florida

Summer Term
2018
ABSTRACT

Two-dimensional materials provide a versatile platform for various electronic and optoelectronic devices, due to their uniform thickness and pristine surfaces. We probe the superior quality of 2D/2D and 2D/3D interfaces by fabricating molybdenum disulfide (MoS$_2$)-based field effect transistors having hexagonal boron nitride (h-BN) and Al$_2$O$_3$ as the top gate dielectrics. An extremely low trap density of $\sim 7 \times 10^{10}$ states/cm$^2$-eV is extracted at the 2D/2D interfaces with h-BN as the top gate dielectric on the MoS$_2$ channel. 2D/3D interfaces with Al$_2$O$_3$ as the top gate dielectric and SiO$_x$ as the nucleation layer exhibit trap densities between $7 \times 10^{10}$ and $10^{11}$ states/cm$^2$-eV, which is lower than previously reported 2D-channel/high-$\kappa$-dielectric interface trap densities. The comparable values of trap time constants for both interfaces imply that similar types of defects contribute to the interface traps. This work establishes the case for van der Waals systems where the superior quality of 2D/2D and 2D/high-$\kappa$ dielectric interfaces can produce high performance electronic and optoelectronic devices.
ACKNOWLEDGMENTS

I would like to thank my advisor Dr. Tania Roy for her unwavering trust and support which always encouraged me to work better. I would like to thank Dr. Reza Abdolvand and Dr. Jiann Shiun Yuaan for being on my committee and for their valuable insights in my research.

I would like to thank my colleagues Hirokjyoti kalita, Sonali Das, Durjoy Dev and Nitin Choudhary for their support throughout my Masters. I also would like to thank Teja Kothamsu from Keysight Technologies for helping me in the measurements setup.

This work would not have been possible if it wasn’t for the support of my friends- Swathi, Nandakishore, Kishan, Archana and Vyshakh. Thanks for believing in me and helping me throughout this journey.

Last but not the least I would like to thank my dad Krishnaprasad, brother Akshay, uncle Kanthareddy and my entire family for their never-ending love and support.
# TABLE OF CONTENTS

LIST OF FIGURES ........................................................................................................ viii
LIST OF TABLES ............................................................................................................ xi

CHAPTER 1: INTRODUCTION TO 2D MATERIALS ............................................................ 1

1.1 Transition metal dichalcogenides (TMDC)............................................................... 1

1.1.1 Crystal Structure of TMDC .............................................................................. 2

1.1.2 2D Materials as Next Generation Channel Material ......................................... 3

1.2 Interface states in 2D materials .............................................................................. 4

1.2.1 Interface states ................................................................................................. 4

1.2.2 Interface Trapped Charges .............................................................................. 5

1.2.3 Origin of Interface states in 2D materials ......................................................... 6

1.3 Objective of the Thesis ......................................................................................... 7

1.4 Overview of thesis .............................................................................................. 7

CHAPTER 2: THE CONDUCTANCE METHOD ............................................................... 8

2.1 D$_{it}$ Extraction Techniques ................................................................................ 8

2.1.1 Low frequency Method (Quasi-static C-V) ..................................................... 8

2.1.2 Castagné and Vapille method ......................................................................... 9

2.1.3 Terman Method .............................................................................................. 9
2.1.4 Gray-Brown Method................................................................. 10
2.2 Conductance technique for Dit extraction.................................................. 10
2.3 Advantages of Conductance technique ...................................................... 15
2.4 Literature on Dit characterization of MoS$_2$............................................. 15
2.5 Chapter Summary................................................................................. 17

CHAPTER 3: MoS$_2$ FET DEVICE FABRICATION ........................................... 19

3.1 Device Structure......................................................................................... 19
  3.1.1 Device Schematic .............................................................................. 19
  3.1.2 Scanning Electron Microscopy (SEM) of MoS$_2$ FET ......................... 20
  3.1.3 Transmission Electron Microscopy (TEM) of MoS$_2$ FET .................... 21
3.2 Fabrication procedure............................................................................. 22
  3.2.1 Alignment marks patterning using photolithography .............................. 22
  3.2.2 Mechanical Exfoliation of MoS$_2$ flakes............................................ 23
  3.2.3 Back-gated MoS$_2$ FET fabrication.................................................. 23
  3.2.4 Top-gated MoS$_2$ FET fabrication .................................................... 24
3.3 Chapter Summary..................................................................................... 25

CHAPTER 4: EXPERIMENTAL RESULTS ..................................................... 26

4.1 Pristine device characteristics ................................................................. 26
  4.1.1 Current-Voltage (I-V) Characteristics ............................................. 26
  4.1.2 C-V and G-V characteristics.......................................................... 29
4.1.3 $D_H$ extraction for pristine devices using the conductance technique .................................. 34

4.2 Effect of forming gas annealing .................................................................................................. 39

4.2.1 I-V Characteristics post FGA ............................................................................................. 40

4.2.2 Post FGA C-V and G-V characteristics .............................................................................. 41

4.2.3 Post FGA $D_H$ extraction by conductance method .............................................................. 43

4.3 Chapter Summary ..................................................................................................................... 46

CHAPTER 5: CONCLUSION ............................................................................................................ 47

5.1 Future Scope ............................................................................................................................. 47

REFERENCES .................................................................................................................................... 48
LIST OF FIGURES

Figure 1: Periodic table depicting the TMDC library available with highlighted fields for chalcogen and transition metal atoms. ................................................................. 2

Figure 2: Crystal structure of MoS$_2$ ....................................................................................... 3

Figure 3: Figure showing surface morphology comparison of 3D and 2D semiconductors. ........ 4

Figure 4: Capacitance stretch-out observed in the MOS-C with the presence of interface states. . 6

Figure 5: Equivalent circuits used for implementing conductance techniques. (a) simplified MOS-C circuit for conductance measurements. (b) simplified circuit derived from (a). (c) measurement circuit. (d) measurement circuit including the tunnel conductance and $G_t$ and series resistance $r_s$ ................................................................. 11

Figure 6: $G_P \omega$ v/s $\omega$ plot obtained from the equation 2.7 (single level) and 2.8 (continuum) and the experimental data .................................................................................................................. 13

Figure 7: Device schematic of MoS$_2$/h-BN FET. ................................................................. 20

Figure 8: Optical microscope image of MoS$_2$/h-BN device. ...................................................... 20

Figure 9: SEM image of the MoS$_2$/h-BN device. ................................................................. 21

Figure 10: cross sectional TEM of a representative monolayer MoS$_2$ FET with h-BN dielectric. ......................................................................................................................... 22

Figure 11: Back-gated I-V of MoS$_2$ FET. Inset: The device on which the back-gated I-V characterization was performed ........................................................................................................ 26

Figure 12: Transfer characteristics of top-gated MoS$_2$/Al$_2$O$_3$ device with AlO$_x$ seeding layer. 27

Figure 13: Top-gated transfer characteristics of MoS$_2$/Al$_2$O$_3$ device with SiO$_x$ seeding layer. . 28

Figure 14: Top-gated transfer characteristics of MoS$_2$ FET with h-BN dielectric. .................... 28
Figure 15: Capacitance model for the MoS$_2$ FET ................................................................. 29
Figure 16: C-V plots for pristine MoS$_2$ FET with AlO$_x$/Al$_2$O$_3$ gate dielectric ..................... 30
Figure 17: C-V plots for pristine MoS$_2$ FET with SiO$_x$/Al$_2$O$_3$ gate dielectric ...................... 31
Figure 18: Pristine C-V plots for h-BN dielectric device .............................................................. 32
Figure 19: G-V characteristics for pristine MoS$_2$ FET with AlO$_x$/Al$_2$O$_3$ gate dielectric ........ 33
Figure 20: G-V characteristics for pristine MoS$_2$ FET with SiO$_x$/Al$_2$O$_3$ gate dielectric .......... 33
Figure 21: G-V characteristics for pristine MoS$_2$ FET with h-BN gate dielectric ...................... 34
Figure 22: $G/\omega$–f curves for gate voltages varied from depletion to accumulation for pristine MoS$_2$
FET with AlO$_x$ seeding layer .................................................................................................. 36
Figure 23: $G/\omega$–f curves for gate voltages varied from depletion to accumulation for pristine
device with SiO$_x$ seeding layer ............................................................................................... 37
Figure 24: $G/\omega$–f curves for gate voltages varied from depletion to accumulation for pristine h-
BN device ....................................................................................................................................... 37
Figure 25: $D_t$ v/s trap position for the pristine Al$_2$O$_3$ and h-BN devices .................................... 38
Figure 26: Trap time constants v/s trap position for the pristine Al$_2$O$_3$ and h-BN devices ......... 39
Figure 27: Post FGA transfer characteristics for MoS$_2$ FET with Al$_2$O$_3$ gate dielectric with SiO$_x$
seeding layer. Inset: Transfer characteristics for MoS$_2$/h-BN device. ................................. 40
Figure 28: Post FGA C-V and G-V characteristics of SiO$_x$/Al$_2$O$_3$ device showing relatively
reduced frequency dispersion in the depletion region ..................................................................... 42
Figure 29: Post FGA C-V and G-V characteristics of h-BN device showing relatively reduced
frequency dispersion in the depletion region .................................................................................. 43
Figure 30: Post FGA $G/\omega$–f curves for gate voltages varied from depletion to accumulation in an
MoS$_2$ FET with SiO$_x$/Al$_2$O$_3$ gate dielectric and h-BN gate dielectric ................................. 44
Figure 31: Post FGA $D_{it}$ v/s trap position exhibiting the decrease in the $D_{it}$ for the SiO$_x$/Al$_2$O$_3$ and h-BN devices.
LIST OF TABLES

Table 1: $D_{it}$ values for MoS$_2$-based devices reported in literature……………………………………16
CHAPTER 1: INTRODUCTION TO 2D MATERIALS

The scaling of silicon has reached its saturation making Moore’s law obsolete. Increased rates of data transfer and performance are the main advantages of transistor scaling. But this transistor scaling comes at a price of pronounced short channel effects, such as increased leakage current, high static power dissipation etc.[1] Because of these aforementioned reasons, substitutes for conventional channel material becomes very critical. Numerous technologies have been studied for decades. With the isolation of single layer of graphene in 2004, two dimensional (2D) materials gained widespread recognition. Graphene is a 2D semi-metallic material with very high carrier mobility \( >50000 \text{ cm}^2/\text{V-s} \) at room temperature having applications in high-speed electronic devices.[2, 3] However, the absence of band-gap in graphene \( i.e \), the absence of OFF state in the graphene field effect transistors (g-FETs) has inspired further exploration of layered materials. Hence, other groups of 2D materials, such as Transitional metal dichalcogenides (TMDCs), hexagonal boron nitride (h-BN), black phosphorus etc. which possess a bandgap have gained prominence in electronic and optoelectronic applications. In this chapter, we discuss TMDCs in detail, with an emphasis on interface states in these 2D materials.

1.1 Transition metal dichalcogenides (TMDC)

The library of TMDCs consists of several members - MoS\(_2\), WS\(_2\), MoSe\(_2\), WSe\(_2\), MoTe\(_2\), WTe\(_2\), etc. which is aptly described in the periodic table as shown in the Figure 1.[4] The family of TMDCs offer various materials ranging from semiconductors (MoS\(_2\), WSe\(_2\)), metals (TaS\(_2\)) and superconductors (FeSe, NbSe\(_2\)). Moreover, the bandgaps of these materials are tunable with the number of layers. For example, monolayer MoS\(_2\) has a bandgap of 1.8 eV, with its bandgap
decreasing with increasing layer numbers. Multilayer MoS₂ has a bandgap of 1.2 eV. Also, most of these TMDCs are direct bandgap at the monolayer level, and become indirect bandgap semiconductors with increasing layer numbers.

Figure 1: Periodic table depicting the TMDC library available with highlighted fields for chalcogen and transition metal atoms.

1.1.1 Crystal Structure of TMDC

2D materials consist of a layer of transition metal M bounded to two layers of chalcogen atom X forming MX₂ which can be semi-conducting, super-conducting or semi-metallic in nature.
Crystalline TMDCs consists of chemically and mechanically robust monolayers of MX\textsubscript{2} bounded by weak van der Waals forces. Typically, a monolayer of TMDC are a few angstroms thick. The aforementioned weak van der Waals forces enable the facile exfoliation of atomically thin layers of TMDCs. This also aides in the assembly of distinct 2D materials to form heterojunctions. The early work started with the mechanical exfoliation of a single layer MoS\textsubscript{2} in 1966 using an adhesive tape\cite{5} followed by chemical exfoliation.\cite{6} Monolayer of MoS\textsubscript{2}, an extensively studied material is \~0.65 nm thick and is shown in Figure 2. Other TMDCs like WS\textsubscript{2}, WSe\textsubscript{2} have also been studied extensively for various electronic and opto-electronic applications.

**1.1.2 2D Materials as Next Generation Channel Material**

Most of the TMDCs have a bandgap in the range of 1-2 eV which makes them perfect for electronic and optoelectronic applications. This tunable band gap enables large switching ratios in the electronic devices. The fact that these materials have a relatively high carrier mobility enables them to be used as channel material for electronic devices.

The narrow mobile charge distribution due to the confinement of the charge carriers to the atomically thin semiconductors has garnered scientific interest. This confinement is modulated easily by the gate voltage which provides excellent gate electrostatics in devices with 2D materials as the channel.\cite{7}
Furthermore, the surface morphology plays a significant role in advocating layered materials as next generation channel material due to the absence of out-of-plane dangling bonds indicating their pristine surfaces shown in the Figure 3. Conventional 3D semiconductors have out-of-plane dangling bonds which act as trap sites resulting in the performance degradation of the FETs. However, in 2D materials, the absence of out-of-plane dangling bonds is a clear indication of a high-quality interface with reduced interface traps. So, 2D material-based semiconductor system is capable of possessing a perfect trap-free interface which is critical for future electronic and optoelectronic applications.

1.2 Interface states in 2D materials

1.2.1 Interface states

A high-quality interface is required for a low subthreshold swing (SS) in field effect transistors, low dispersion in high frequency devices, high performance in solar cells and increased efficiency in optoelectronic devices. The full potential of the gate dielectric cannot be realized often, due to the potential drop across interface traps between the gate dielectric and the
semiconductor. Therefore, it becomes essential to have an insight about the interface states of any semiconductor system for high performance devices.

Interface states arise from the trapped charges at the semiconductor/dielectric interface. These charges can be mobile ionic or fixed charges within the dielectric created during the fabrication process. The trap centers for the charges originate from the presence of dangling bonds in 3D semiconductors. These trap centers play an active role in determining the electronic properties of the device.

### 1.2.2 Interface Trapped Charges

It has been stated that interface-trapped charge $Q_{it}$ are present within the forbidden energy gap due to the interruption of the periodic lattice structure of a crystal.[8] An interface trap becomes a donor interface trap by donating an electron and an acceptor interface trap by receiving an electron. The following expressions represent the distribution functions for the interface traps which are similar to those for the bulk impurity levels.

$$F_{SD}(E_t) = \frac{1}{1 + g \exp \left( \frac{E_F - E_t}{kT} \right)} \quad (1.1)$$

For the donor interface traps where $E_t$ is the interface trap energy and $g$ ground state degeneracy. The $g$ for the acceptor trap is 2 and for the donor trap is 4.

$$F_{SD}(E_t) = \frac{1}{1 + \frac{1}{g} \exp \left( \frac{E_F - E_t}{kT} \right)} \quad (1.2)$$

The interface trap levels move with the conduction and the valence bands whereas the Fermi level remains fixed as the voltage bias is applied.[8] The movement of the trap levels is either up or down and when the interface trap crosses the Fermi level, the change in the charge
occurs. This change in the charge contributes to the capacitance of metal-insulator-semiconductor (MIS) and the change is reflected in the capacitance-voltage curve shown in the Figure 4.

![Capacitance stretch-out observed in the MOS-C with the presence of interface states.](image)

**Figure 4**: Capacitance stretch-out observed in the MOS-C with the presence of interface states.

### 1.2.3 Origin of Interface states in 2D materials

It is believed that the absence of out-of-plane dangling bonds contributes to high quality 2D channel/dielectric interface. However, the inherent defects present in the 2D materials will play a significant role in introducing the trap centers which degrades the performance of the device.

#### 1.2.3.1 Defects in MoS$_2$

Despite the fact that a number of TMDCs show semiconducting behavior, MoS$_2$ is the most widely studied. This is due its availability in nature and the ease with which it can be mechanically exfoliated. The origin of the defects in MoS$_2$ has been extensively studied. During mechanical exfoliation of MoS$_2$, it has been observed that pits are formed on the surface of the material.[9] This variation in the morphology is one of the reasons for the formation of defects. Furthermore, the defects in MoS$_2$ are also caused by stoichiometric variations in the same layer of the material. These stoichiometric variations are because of the sulfur vacancies[9, 10] observed in the lattice
of MoS$_2$ and also due to the presence of impurities like alkali metals[9] in the bulk crystal. Presence of these defects give rise to interface traps in the energy gap of the semiconductor. This degrades the performance of the device by causing the local carrier depletion and hence decreases the current in the devices. So, it becomes very critical to quantify the density of the interface states ($D_{it}$).

1.3 Objective of the Thesis

In this thesis we investigate the quality of MoS$_2$/dielectric interface by quantifying the interface states using the conductance method. The experiment is conducted by using the MoS$_2$ FETs as the test structures to implement the conductance technique. We investigate the interface traps at MoS$_2$/h-BN and MoS$_2$/Al$_2$O$_3$ interface.

1.4 Overview of thesis

This work emphasizes on the extraction of density of interface traps ($D_{it}$) in MoS$_2$ based system. Chapter two deals with the extraction technique used in this work and the literature survey on the various techniques used to extract $D_{it}$ in MoS$_2$ systems. Chapter three consists of detailed description of the device structure and fabrication. Chapter four deals with the experimental results, which include C-V, G-V characterizations of the devices, interface trap extraction, and effect of forming gas annealing on trap densities. Chapter five explains the future scope of this work.
CHAPTER 2: THE CONDUCTANCE METHOD

In this chapter we discuss the techniques by which $D_{it}$ can be extracted in a semiconducting system. The conductance technique for $D_{it}$ extraction is emphasized here, and its advantages over other techniques are noted. Finally, we provide a comprehensive overview of the interface trap densities extracted using various techniques for MoS$_2$-based devices that are reported in the literature.

2.1 $D_{it}$ Extraction Techniques

Various techniques are implemented to extract $D_{it}$. The $D_{it}$ is extracted using a Metal-Semiconductor-Oxide Capacitor (MOS-C). There are several techniques to extract the $D_{it}$ such as low frequency methods and high frequency methods.

2.1.1 Low frequency Method (Quasi-static C-V)

The low frequency method is also known as the Quasi-Static Capacitance-Voltage (C-V) method.[11] In this method a low frequency C-V curve is compared with a high frequency C-V curve where the traps are assumed to be unresponsive. The low frequency capacitance denoted by $C_{lf}$ is given by equation 2.1 for the depression-inversion region. Here, $C_{ox}$ is the oxide capacitance, $C_S$ is the semiconductor capacitance and the interface capacitance is given by $C_{it}$. Followed by this, the $D_{it}$ is extracted by the equation 2.2[11]

$$C_{lf} = \left[ \frac{1}{C_{ox}} + \frac{1}{C_{S}+C_{it}} \right]^{-1}$$

$$D_{it} = \frac{1}{q^2} \left[ \frac{C_{ox} C_{lf}}{C_{ox} - C_{lf}} - C_S \right]$$

(2.1)  

(2.2)
The $C_S$ is calculated as a function of surface potential $\phi_S$ and gate voltage which introduces uncertainty in the estimation of $C_S$. Therefore, a simplified approach called as Castagné and Vapille method is used.[11]

### 2.1.2 Castagné and Vapille method

In this approach, the $C_S$ is calculated from the high-frequency C-V curve given in the equation 2.3 where $C_{hf}$ is the high frequency capacitance.[11]

$$C_S = \frac{C_{ox}C_{hf}}{C_{ox} - C_{hf}}$$  \hspace{1cm} (2.3)

By substituting equation 2.3 in 2.1, the $D_{it}$ is extracted as a function of capacitances at low and high frequencies as shown in equation 2.4.

$$D_{it} = \frac{C_{ox}}{q^2} \left[ \frac{C_{lf}/C_{ox}}{1 - C_{lf}/C_{ox}} - \frac{C_{hf}/C_{ox}}{1 - C_{hf}/C_{ox}} \right]$$  \hspace{1cm} (2.4)

### 2.1.3 Terman Method

This is one of the high-frequency methods employed to extract $D_{it}$. Here the capacitance is measured at high frequency assuming that interface traps do not respond to the high frequency ac signal but respond only to the slowly varying dc voltage.[11] The high frequency C-V stretch out is observed as a function of varying gate voltage. The stretch-out is due to the change in the trap occupancy. The $D_{it}$ is given by the equation 2.5

$$D_{it} = \frac{C_{ox}}{q^2} \left[ \frac{d\Delta V/G}{d\phi_S} \right]$$  \hspace{1cm} (2.5)

This technique is applicable for extracting the $D_{it}$ of $10^{10}$/cm$^2$-eV and above. The technique tends to be inaccurate for thin dielectrics with non-negligible interface state capacitance, since it assumes the interface state capacitance to be zero.
2.1.4 Gray-Brown Method

This is a high-frequency capacitance technique measured at reduced temperatures. Typically, the measurements are performed at 77 K with a measurement frequency of 200 MHz. The reduction in the temperature causes the Fermi level to shift towards the majority carrier band edge and also increases the interface trap time constant ($\tau_{it}$).[11]

2.2 Conductance technique for $D_{it}$ extraction

In the conductance technique, the $D_{it}$ is determined in the depletion and weak inversion region of the band-gap. This is a comprehensive extraction technique since it provides information regarding the surface potential fluctuations along with the capture cross-sections of the majority carriers. This technique is implemented by measuring the parallel conductance of the MOS-C as a function of frequency and the bias voltage applied. A more accurate estimate $D_{it}$ is obtained since it is implemented using the parallel conductance.

The conductance technique, introduced by Nicollian and Goetzberger in 1967, is a sensitive method which yields accurate estimate of $D_{it}$. This technique is capable of determining the $D_{it}$ of $10^9$ /cm$^2$-eV and lower because of the response of the interface traps for applied bias voltage and frequency. This technique does not require any modeling to extract the $D_{it}$ values, and the $D_{it}$ can be obtained directly from the experimental results. The conductance method involves measuring the parallel conductance as a function of frequency and the bias voltage applied. The interface trap density is derived from the loss mechanism of the charge carriers by the capture and emission through the interface traps. The conductance method does not necessarily require a MOS-C structure and can be implemented on FET structures directly.

The simplified circuit of MOS-C shown in the Figure 5(a) consists of 3 different capacitances, $C_{ox}$ is the oxide capacitance, $C_S$ is the semiconductor capacitance and the interface
capacitance is given by $C_{it}$. At the semiconductor/dielectric interface, the capture and emission of the charge carriers is due to the interface traps implying the process to be lossy which is represented by $R_{it}$. Figure 5(a) represents the simplified circuit. Here the $R_{it}$ and $C_{it}$ are replaced by a parallel conductance as shown in Figure 5(b) and $C_S$ is replaced by $C_P$.

$$C_P = C_S + \frac{C_{it}}{1+(\omega \tau_{it})^2}$$  \hspace{1cm} (2.6)

Here, $C_{it} = q^2 D_{it}$, $\omega = 2\pi f$ ($f$: measurement frequency), the interface trap time constant is given by $\tau_{it}$; $\tau_{it} = R_{it} C_{it}$

![Diagram of equivalent circuits](image)

Figure 5: Equivalent circuits used for implementing conductance techniques. (a) simplified MOS-C circuit for conductance measurements. (b) simplified circuit derived from (a). (c) measurement circuit. (d) measurement circuit including the tunnel conductance and $G_t$ and series resistance $r_s$.

The parallel conductance is then divided by $\omega$ to give the equation,

$$\frac{G_P}{\omega} = \frac{q\omega \tau_{it} D_{it}}{1+(\omega \tau_{it})^2}$$ \hspace{1cm} (2.7)
The above equation is for the interface traps in one energy level. However, the interface traps at SiO₂/Si interface are distributed throughout the energy gap of Si. Therefore, the parallel conductance is normalized due to constant time dispersion. This normalization is carried out because the charge capture and emission are caused by the traps which are a few \( kT/q \) levels above and below the Fermi level. The normalized conductance is given below.

\[
\frac{G_p}{\omega} = \frac{qD_{it}}{2\omega\tau_{it}} \ln[1 + (\omega\tau_{it})^2]
\]  \hspace{1cm} (2.8)

The equations 2.7 and 2.8 indicate that the conductance is relatively easy to interpret than the capacitance due to the absence of \( C_s \). The measured conductance is normalized and is a function of \( \omega \). Peak \( \frac{G_p}{\omega} \) is obtained when \( \omega = \frac{1}{\tau_{it}} \) and the corresponding \( D_{it} \) is given by \( D_{it} = \frac{2G_p}{q\omega} \). From the above equation, \( \omega \approx \frac{2}{\tau_{it}} \) and \( D_{it} \approx \frac{5G_p}{q\omega} \) at maximum. Therefore, the \( D_{it} \) is determined at the maximum peak in \( \frac{G_p}{\omega} \) plot against \( \omega \). For the corresponding \( \omega \), \( \tau_{it} \) is calculated which provides an insight regarding the type of the traps at the interface.

From the Figure 6, it is evident that the \( \frac{G_p}{\omega} \) plot is broader when compared to the trap profile extracted from the equation 2.8. It is attributed to the dispersion in the interface time constant caused by the surface potential fluctuations. These fluctuations are caused by the non-uniformities in the oxide charges, interface traps and doping density.
Figure 6: $\frac{G_P}{\omega}$ v/s $\omega$ plot obtained from the equation 2.7 (single level) and 2.8 (continuum) and the experimental data.

Therefore, surface potential fluctuations need to be accounted for the extraction of the trap profile. In such cases, $\frac{G_P}{\omega}$ is given by,

$$\frac{G_P}{\omega} = \int_{-\infty}^{\infty} \frac{D_{lt}}{\omega r_{it}} \ln \left[ 1 + (\omega r_{it})^2 \right] P(U_S) \, dU_S$$  \hspace{1cm} (2.9)

Where, $P(U_S)$ is the surface potential fluctuation probability distribution which is given by,

$$P(U_S) = \frac{1}{\sqrt{2\pi\sigma^2}} \exp \left( -\frac{(U_S - \bar{U}_S)^2}{2\sigma^2} \right)$$  \hspace{1cm} (2.10)

Where, $\sigma$ is the standard deviation whereas, $\bar{U}_S$ is the normalized mean surface potential.

Therefore, the expression for the $D_{lt}$ as a function of $\frac{G_P}{\omega}$ is given by

$$D_{lt} \approx \frac{2.5}{q} \left( \frac{G_P}{\omega} \right)_{\text{max}}$$  \hspace{1cm} (2.11)
The parallel conductance of a device is measured simultaneously with the parallel capacitance. Therefore, assuming negligible series resistance, $\frac{G_P}{\omega}$ can be calculated in terms of measured capacitance $C_m$, measured conductance $G_m$ and the oxide capacitance $C_{ox}$ which is given by

$$\frac{G_P}{\omega} = \frac{\omega G_m C_{ox}^2}{G_m^2 + \omega^2 (C_{ox} - C_m)^2} \quad (2.12)$$

During the conductance measurements, the signal amplitude is kept at 50 mV or lower to prevent harmonics. The presence of these harmonics in the signal frequency can give false conductance values. One more noteworthy point would be that, for given $D_\ell t$ the corresponding conductance depends on the area of the device. For thin oxides, the series resistance will be considered. So, now the circuit consists of tunnel conductance $G_t$ and series resistance $r_s$. Therefore, $\frac{G_P}{\omega}$ is given as

$$\frac{G_P}{\omega} = \frac{\omega (G_C - G_t) C_{ox}^2}{G_C^2 + \omega^2 (C_{ox} - C_C)^2} \quad (2.13)$$

Where,

$$C_C = \frac{C_m}{(1 - r_s G_m)^2 + (\omega r_s C_m)^2} \quad (2.14)$$

$$G_C = \frac{\omega^2 r_s C_m C_C - G_m}{r_s G_m - 1} \quad (2.15)$$

where, $C_m$ and $G_m$ are the measured capacitance and conductance. The series resistance is obtained by measuring the conductance and the capacitance in the accumulation region which is given by

$$r_s = \frac{G_{ma}}{G_{ma}^2 + \omega^2 C_{ma}^2} \quad (2.16)$$
where the $G_{ma}$ and $C_{ma}$ are the conductance and the capacitance measured in accumulation region.

To determine the tunnel conductance, equation 2.15 is considered as $\omega \to 0$, equation 2.13 is reduced to equation 2.12, where $r_3 = G_t = 0$.

### 2.3 Advantages of Conductance technique

The $D_{it}$ extracted by conductance technique is accurate when compared with the capacitance methods. The complexity increases when the $D_{it}$ is extracted by the capacitance methods because, the capacitance of a MOS-C consists of oxide capacitance, semiconductor capacitance, depletion-layer capacitance and interface capacitance. Therefore, extracting the $D_{it}$ as a function of voltage and frequency through the capacitance measurements might give rise to inaccuracies because the difference of the capacitance needs to be calculated. This is not the case in the conductance technique, since the conductance is directly translatable to the response of the interface traps as the function of voltage and frequency.

The conductance technique is capable of probing the $D_{it}$ of $\sim 10^9$ states/cm$^2$-eV and lower and entire band gap. This technique is capable of probing the interface traps in depletion and weak-inversion region.

The $D_{it}$ is extracted based on the measured conductance of the MOS-C. No assumptions are made to quantify the $D_{it}$. Also, no model is used to extrapolate the $D_{it}$ from the measured capacitance of the MOS-C as in the case of Terman Method. It is because of these advantages that we chose to use the conductance technique to analyze the interface states in MoS2-based FETs.

### 2.4 Literature on $D_{it}$ characterization of MoS$_2$

Many different techniques have been used to extract $D_{it}$ for MoS$_2$ based devices. Table 1 summarizes the $D_{it}$ values obtained and the techniques used to extract the $D_{it}$. 

15
Table 1: \(D_{it}\) values for MoS\(_2\)-based devices reported in literature.

<table>
<thead>
<tr>
<th>Device Structure</th>
<th>Thickness</th>
<th>Type of MoS(_2)</th>
<th>Method of (D_{it}) Extraction</th>
<th>(D_{it}) Value (states/cm(^2)-eV)</th>
</tr>
</thead>
<tbody>
<tr>
<td>MoS(_2)/HfO(_2)[12]</td>
<td>7-layer MoS(_2) 13 nm HfO(_2) 4-layer MoS(_2) 8 nm HfO(_2)</td>
<td>Exfoliated</td>
<td>High low frequency method and multi-frequency</td>
<td>1.2 \times 10^{13} 2 \times 10^{11} – 2 \times 10^{13}</td>
</tr>
<tr>
<td>MoS(_2)/HfTiO[13]</td>
<td>50-layers (32.5 nm) MoS(_2) 39.65nm HfTiO 1-layer (0.85 nm) MoS(_2)</td>
<td>Transferred by scotch tape</td>
<td>From SS</td>
<td>5.58 \times 10^{12}</td>
</tr>
<tr>
<td>MoS(_2)/Al(_2)O(_3)[14]</td>
<td>1nm Al(_2)O(_3) seeding layer 15 nm Al(_2)O(_3) dielectric</td>
<td>CVD</td>
<td></td>
<td>1.6 \times 10^{13}</td>
</tr>
<tr>
<td>MoS(_2)/h-BN[15]</td>
<td>Single or bilayer MoS(_2)</td>
<td>Exfoliated by scotch tape</td>
<td>observed noise magnitude</td>
<td>6 \times 10^{10} - 1 \times 10^{12}</td>
</tr>
<tr>
<td>MoS(_2)/h-BN[16]</td>
<td>Tri-layer MoS(_2)</td>
<td>Exfoliated</td>
<td></td>
<td>\sim 10^{12}</td>
</tr>
<tr>
<td>MoS(_2)/ZrO(_2)[17]</td>
<td>Few layers MoS(_2) 5.8nm ZrO(_2)</td>
<td>Transferred</td>
<td>From SS</td>
<td>1.7 \times 10^{12}</td>
</tr>
<tr>
<td>MoS(_2)/HfO(_2)[18]</td>
<td>Monolayer to tri-layer (0.7nm to 2.1nm) MoS(_2) 10nm HfO(_2)</td>
<td>Exfoliated</td>
<td>From SS</td>
<td>5 \times 10^{12}</td>
</tr>
<tr>
<td>MoS(_2)/Al(_2)O(_3)[19]</td>
<td>30nm MoS(_2) 50nm Al(_2)O(_3)</td>
<td>Exfoliated</td>
<td>From SS</td>
<td>2.6 \times 10^{11}</td>
</tr>
<tr>
<td>Device Structure</td>
<td>Thickness</td>
<td>Type of MoS$_2$</td>
<td>Method of $D_\text{it}$ Extraction</td>
<td>$D_\text{it}$ Value (states/cm$^2$-eV)</td>
</tr>
<tr>
<td>------------------</td>
<td>-----------</td>
<td>----------------</td>
<td>-----------------------------------</td>
<td>--------------------------------------</td>
</tr>
<tr>
<td>MoS$_2$/SiN$_x$[20]</td>
<td>140-layers MoS$_2$ 250nm SiN$_x$</td>
<td>Exfoliated</td>
<td>From SS</td>
<td>$1.14\times10^{13}$</td>
</tr>
<tr>
<td>MoS$_2$/SiO$_x$/SiN$_x$[20]</td>
<td>125-layers MoS$_2$ 50nm SiO$_x$ 200nm SiN$_x$</td>
<td>Exfoliated</td>
<td>From SS</td>
<td>$2.13\times10^{12}$</td>
</tr>
<tr>
<td>MoS$_2$/thermal SiO$_2$[20]</td>
<td>154-layers MoS$_2$ 100 nm SiO$_2$</td>
<td>Exfoliated</td>
<td>From SS</td>
<td>$3.32\times10^{12}$</td>
</tr>
<tr>
<td>MoS$_2$/Al$_2$O$_3$[21]</td>
<td>7 – 8 nm MoS$_2$ 10 nm Al$_2$O$_3$</td>
<td>Exfoliated</td>
<td>Terman</td>
<td>$1\times10^{12}$</td>
</tr>
<tr>
<td>MoS$_2$/HfO$_2$[21]</td>
<td>7 – 8 nm MoS$_2$ 10 nm HfO$_2$</td>
<td>Exfoliated</td>
<td>Terman</td>
<td>$2\times10^{12}$</td>
</tr>
<tr>
<td>MoS$_2$/HfO$_2$[10]</td>
<td>Monolayer MoS$_2$ 5 nm HfO$_2$</td>
<td>CVD</td>
<td>High-low frequency method</td>
<td>$7.03\times10^{11}$</td>
</tr>
<tr>
<td>MoS$_2$/Al$_2$O$_3$[22]</td>
<td>11.3 nm MoS$_2$ 30 nm Al$_2$O$_3$</td>
<td>Exfoliated</td>
<td>Low Frequency Noise characterization</td>
<td>$1.8\times10^{12}$</td>
</tr>
<tr>
<td>MoS$_2$/Al$_2$O$_3$[23]</td>
<td>15nm MoS$_2$ 16nm Al$_2$O$_3$</td>
<td>Exfoliated</td>
<td>using CNF Model</td>
<td>$2.4\times10^{12}$</td>
</tr>
</tbody>
</table>

**2.5 Chapter Summary**

In summary, we have discussed different techniques that can be employed to extract the $D_\text{it}$. Of all the techniques discussed, conductance technique is the most reliable method. Therefore, we have employed this technique to extract $D_\text{it}$ at MoS$_2$/h-BN and MoS$_2$/Al$_2$O$_3$ devices. From the
overview of the different techniques employed to study the $D_{it}$ in the MoS$_2$ based systems, it can be understood that the conductance technique has not been employed yet to extract MoS$_2$ $D_{it}$. 
CHAPTER 3: MoS$_2$ FET DEVICE FABRICATION

In this chapter we discuss the structure of the MoS$_2$ transistor adapted for the $D_{lt}$ extraction. We have fabricated MoS$_2$ transistors with 2D h-BN as the gate dielectric to investigate a 2D/2D interface. 2D/3D interfaces have also been fabricated using Al$_2$O$_3$ as the high-κ gate dielectric. The specific steps in the device fabrication are outlined here.

3.1 Device Structure

For the $D_{lt}$ extraction, the 2D channel considered is MoS$_2$ and h-BN is the 2D dielectric used. The $D_{lt}$ is also extracted at MoS$_2$ channel/ hi-k dielectric like Al$_2$O$_3$. To quantify the density interface states in 2D channel/ dielectric interface, dual gated MoS$_2$ Field Effect Transistor (FET) is fabricated.

3.1.1 Device Schematic

The schematic of the MoS$_2$/h-BN FET is as shown in the Figure 7. The top gate contact is patterned such that there are underlapped regions near the source and drain. These regions are kept populated with electrons using the back gate voltage, so that series resistance can be minimized during capacitance and conductance measurements. The optical microscope image of the MoS$_2$/h-BN device is shown Figure 8.
3.1.2 Scanning Electron Microscopy (SEM) of MoS$_2$ FET

The SEM image of the complete device is shown in the Figure 9. The SEM was performed with Zeiss Ultra 55 SEM.
3.1.3 Transmission Electron Microscopy (TEM) of MoS$_2$ FET

To confirm the quality of layer stacking, cross-sectional transmission electron microscopy (TEM) is performed on a representative device with monolayer MoS$_2$ as the channel. Initially, a cross-section sample was lifted off using Helios Nanolab 600 Dual Beam Focused Ion Beam Milling System followed by the TEM characterization using JEOL 2010F operated at 200 kV acceleration voltage. Figure 10 shows the cross-sectional TEM micrograph of the MoS$_2$/h-BN layer stacked on SiO$_2$ substrate followed by Nickel top gate. Monolayer MoS$_2$ can be clearly seen on the SiO$_2$ substrate. Multilayer structure stacked on the MoS$_2$ layer had a interlayer spacing of ~0.34 nm corresponding to h-BN, and the van der Waals interface between MoS$_2$ and h-BN was clean, highly coherent and free of any structural disorders.
Figure 10: cross sectional TEM of a representative monolayer MoS\textsubscript{2} FET with h-BN dielectric.

(Courtesy: Supriya Koul and Professor Akihiro Kushima, UCF)

3.2 Fabrication procedure

The MoS\textsubscript{2} FETs are fabricated using multiple lithography processes. E-beam lithography is used to fabricate dual gated MoS\textsubscript{2} FETs.

3.2.1 Alignment marks patterning using photolithography

The starting substrate for the device fabrication is 260 nm thermally grown SiO\textsubscript{2} on p+ Si wafers. The device fabrication starts with the alignment marks patterning using conventional photolithography on the SiO\textsubscript{2}/Si substrate. These marks are used to locate 2-7 nm thick MoS\textsubscript{2} flakes, and are used during e-beam lithography for the alignment. The patterning is carried out with positive resist S1813 from Microposit. The resist is spin-coated at a speed of 4500 rpm with an acceleration of 300 rpm/sec for 1 minute. The soft-baking is carried out for spin-coating for 1 min at 115 °C. MJB 4 Karl Suss Aligner is used for the alignment and exposure. The exposure dose is 10.21 mJ/cm\textsuperscript{2} and the exposure is done for 9 s. After the exposure, the patterns are developed in CD-26 resist developer for 35 s.
3.2.2 Mechanical Exfoliation of MoS\textsubscript{2} flakes

The device fabricated consists of MoS\textsubscript{2} flake (SPI supplies) 3-10 layers thick as the channel material. The MoS\textsubscript{2} flake is isolated by mechanical exfoliation using Scotch-tape method where few layers of MoS\textsubscript{2} are cleaved from the bulk MoS\textsubscript{2} using scotch tape and then transferred on the patterned Si/SiO\textsubscript{2} substrate. After the exfoliation, the flakes of desired thickness are located on the substrate.

3.2.3 Back-gated MoS\textsubscript{2} FET fabrication

The patterning of the device is carried out by e-Beam lithography. This lithography procedure requires the mask design for individual flakes. The sample is spin-coated with MicroChem 950 PMMA C4 e-beam resist (positive). The spin coating is done at 2 different speeds. At first, the resist is spun at 500 rpm for 30 s followed by 4000 rpm for 30 s. The sample is then soft-baked at 130 °C for 3 mins. The e-beam lithography is carried out using Zeiss Ultra 55 scanning electron microscope (SEM) integrated with Nanometer Pattern Generation System (NPGS). The contact fingers are smaller and are written at a current ~ 100 nA with a dose of 350 μC/cm\textsuperscript{2} while the contact pads which are larger are written with a current of ~1.4 nA and the similar dose as before. Then, the development is done by immersing the sample in a mixture of MIBK: IPA in the ratio of 1:3 for 45 seconds followed by an IPA bath for 1 min.

The evaporation is carried out after the patterning for the lift-off of the metal. The e-beam evaporation is carried out in Thermionics system. 30 nm of Nickel is deposited at a pressure of 4 × 10\textsuperscript{-6} Torr as the contact metal. After the deposition, lift-off is carried out by immersing the sample in the Acetone bath at 60 °C for 25 mins. This completes the fabrication of back-gated MoS\textsubscript{2} FET.
3.2.4 Top-gated MoS$_2$ FET fabrication

3.2.4.1 Dielectric deposition by dry transfer of h-BN flakes

The top-gated FET fabrication procedure is explained as follows. For the fabrication of the MoS$_2$ FET with h-BN top gate dielectric, a dry transfer technique is used. For the dry transfer of h-BN, mechanical exfoliation of h-BN using scotch tape is carried out on the visco-elastic stamp. Followed by this, mapping of h-BN flakes of thickness $\sim$13 nm is carried out. After this, the h-BN flakes are transferred on the MoS$_2$ channel. Then, the top gate contact is patterned using e-beam lithography and 30 nm Ni is deposited as the contact metal followed by lift-off in an acetone bath. This marks the end of the MoS$_2$/h-BN device fabrication.

3.2.4.2 Dielectric deposition by Atomic Layer Deposition (ALD)

Due to the absence of dangling bonds, the deposition of dielectrics by Atomic Layer Deposition (ALD) is not uniform. Therefore, nucleation layer is deposited prior to ALD for functionalizing the top surface of MoS$_2$.\cite{24-26} This nucleation layer aides for the uniform deposition of the dielectric. Two different nucleation layers, such as AlO$_x$ and SiO$_x$ of 1.5 nm thickness are deposited.

For the seeding layer deposition, 1.5 nm Al and SiO$_x$ is e-beam evaporated and left to oxidize in air for a few minutes. The stoichiometric composition of the oxide layer formed is AlO$_x$ and SiO$_x$. Followed by this, ALD (Cambridge Nanotech) is carried out. 8.5 nm thick Al$_2$O$_3$ is deposited at 250 $^\circ$C at 85 mTorr using Trimethylaluminium (TMA) and H$_2$O precursors. After the dielectric deposition, the top-gate is patterned by e-beam lithography and 30 nm Ni e-beam evaporated as the contact metal, followed by lift-off.
3.3 Chapter Summary

Dual gated MoS$_2$ FETs are fabricated. 3 types of devices were fabricated for the $D_{hh}$ extraction. Devices with Al$_2$O$_x$ gate dielectric were fabricated using AlO$_x$ and SiO$_x$ seeding layer. MoS$_2$ FETs with h-BN gate dielectric were also fabricated.
CHAPTER 4: EXPERIMENTAL RESULTS

In this chapter, we report the capacitance-voltage and conductance-voltage characteristics of the fabricated devices. We extract the interface trap densities using the conductance method for the MoS$_2$ FETs. Initially, the $D_{it}$ was extracted for the pristine devices and is followed by the studies of effect of forming gas annealing on the $D_{it}$.

4.1 Pristine device characteristics

Before the dielectric deposition and further processing, the characteristics of the back-gated MoS$_2$ FET is tested to investigate the conductivity of the MoS$_2$ flake because the micro-tears between the electrodes will cause the open circuit restricting the flow of the current. The back-gated current-voltage (I-V) characteristics of a representative MoS$_2$ FET shown in the Figure 11.

![Figure 11: Back-gated I-V of MoS$_2$ FET. Inset: The device on which the back-gated I-V characterization was performed.](image)

4.1.1 Current-Voltage (I-V) Characteristics

After the completion of fabrication of the top-gated devices, the electrical measurements were performed on the devices. At first the top-gated I-V is carried out. For this measurement, the
bias is applied on the top-gate by keeping the back-gate at 0 V. Figures 12, 13 and 14 show the transfer characteristics of the FETs with AlO$_x$/Al$_2$O$_3$, SiO$_x$/Al$_2$O$_3$ and h-BN top gate dielectrics, respectively at $V_D = 50 \text{ mV} \& 1 \text{ V}$. The subthreshold swing (SS) is calculated from the I-V characteristics. The SS of the MoS$_2$ FET with AlO$_x$/Al$_2$O$_3$ gate dielectric is 160 mV/decade (Figure 12), with SiO$_x$/ Al$_2$O$_3$ gate dielectric is 180 mV/decade (Figure 13) while the SS of the device with h-BN gate dielectric is 140 mV/decade (Figure 14).

![Figure 12: Transfer characteristics of top-gated MoS$_2$/Al$_2$O$_3$ device with AlO$_x$ seeding layer.](image)

---

27
Figure 13: Top-gated transfer characteristics of MoS$_2$/Al$_2$O$_3$ device with SiO$_x$ seeding layer.

Figure 14: Top-gated transfer characteristics of MoS$_2$ FET with h-BN dielectric.
After the I-V characterization, Capacitance-Voltage (C-V) measurements are carried out. For these measurements, we shorted the source and drain and connected them to the ‘low’ terminal of the capacitance measurement unit (CMU). We modified the bias on the ‘high’ terminal of the capacitance measurement unit that was connected to the top gate electrode. The back gate was grounded at 0 V. Since in our depletion mode MoS\(_2\) FET, the channel is quite populated with electrons at \(V_{BG} = 0\) V, keeping the underlapped channel regions conductive.

### 4.1.2 C-V and G-V characteristics

Figure 15 shows the equivalent circuit model of the capacitances and resistances that come into play while measuring the capacitance between the gate electrode and the source/drain electrodes. The MoS\(_2\) FET consists of various capacitances: semiconductor capacitance \(C_{body}\), interface capacitance \(C_{it}\) and oxide capacitance \(C_{G}\) represented by \(C_m\) and corresponding conductance \(G_m\).

![Figure 15: Capacitance model for the MoS\(_2\) FET.](image)

Before, the measurements the CMU is calibrated first. The CMU is first open calibrated by keeping all the terminals open. Followed by this, the short calibration is performed by connecting
the top-gate terminal and the common source and drain terminal on a metal bar. The calibration is performed for the frequencies ranging between 1 kHz to 5 MHz. After this, the C-V program is executed in open circuit to make sure the RMS value of the capacitance as measured by the CMU is ~0 F. The device is always swept from accumulation to depletion region for multiple discrete frequencies \( \text{viz.,} 1 \text{ kHz, 5 kHz, 10 kHz, 20 kHz, 50 kHz, 100 kHz and 200 kHz} \). The gate voltage is superimposed with an ac signal of amplitude 50 mV. The measurements were done with high integration factor (slow) which allows the interface traps to respond to the applied bias. The C-V characteristics of the pristine MoS\textsubscript{2}/Al\textsubscript{2}O\textsubscript{3} devices with AlO\textsubscript{x} and SiO\textsubscript{x}, and the MoS\textsubscript{2}/h-BN device are shown in the Figures 16, 17 and 18 respectively.

![C-V plots for pristine MoS\textsubscript{2} FET with AlO\textsubscript{x}/Al\textsubscript{2}O\textsubscript{3} gate dielectric.](image)

Figure 16: C-V plots for pristine MoS\textsubscript{2} FET with AlO\textsubscript{x}/Al\textsubscript{2}O\textsubscript{3} gate dielectric.
Figure 17: C-V plots for pristine MoS₂ FET with SiOₓ/Al₂O₃ gate dielectric.

As observed from the plots the dispersion in the depletion region is a clear signature of the interface trap response to the applied gate bias. The high capacitance in the accumulation region is attributed to the parasitic capacitances because of the ungated region adjacent to source and drain. The Al₂O₃ device with AlOₓ seeding layer show more dispersion in comparison with other two devices indicating that AlOₓ seeding layer has more traps.
Figure 18: Pristine C-V plots for h-BN dielectric device.

The conductance-voltage (G-V) characteristics are shown in the Figures 19, 20 and 21 for AlO_x/Al_2O_3, SiO_x/Al_2O_3 and h-BN gated devices respectively. The conductance variation as a function of frequency is observed. Distinct increase in the peak is observed with the increase in frequency. Also, the device with AlO_x seeding layer shows the maximum conductance of 53 nS at 200 kHz when compared to SiO_x and h-BN device at the same frequency.
Figure 19: G-V characteristics for pristine MoS$_2$ FET with AlO$_x$/Al$_2$O$_3$ gate dielectric.

Figure 20: G-V characteristics for pristine MoS$_2$ FET with SiO$_x$/Al$_2$O$_3$ gate dielectric.
Figure 21: G-V characteristics for pristine MoS$_2$ FET with h-BN gate dielectric.

After the C-V measurements, the capacitance and conductance are measured at a constant voltage bias as a function of frequency. Now the conductance technique is implemented to extract the $D_{it}$.

4.1.3 $D_{it}$ extraction for pristine devices using the conductance technique

The conductance method was implemented at room temperature in air. The corrected capacitance $C_c$ and conductance $G_c$ need to be extracted first since the device possesses series resistances from the ungated regions and from the contacts. The series resistance is obtained by biasing the device in accumulation, and then the following expression is applied:

$$R_S = \frac{g_{ma}}{\frac{g_{ma}^2}{c_{ma}^2} + \omega^2 c_{ma}^2}$$  \hspace{1cm} (4.1)
\( G_{ma} \) and \( C_{ma} \) are the measured conductance and capacitance, respectively, in the accumulation region, \( \omega = 2\pi \times \text{frequency} \). Followed by this, the series resistance factor denoted by \( a \) is calculated as \( a = G_m - (G_m^2 + \omega^2 C_m^2) R_S \), where \( G_m \) and \( C_m \) are the measured conductance and capacitance, respectively. \( G_c \) and \( C_c \) can be then calculated as:

\[
G_c = \frac{(G_m^2 + \omega^2 C_m^2)a}{a^2 + \omega^2 C_m^2} \tag{4.2}
\]

\[
C_c = \frac{(G_m^2 + \omega^2 C_m^2)c_m}{a^2 + \omega^2 c_m^2} \tag{4.3}
\]

Now \( G_p/\omega \) can be calculated as follows:

\[
\frac{G_p}{\omega} = \frac{\omega G_c C_c^2}{G_c^2 + \omega^2 (C_G - C_C)^2} \tag{4.4}
\]

Here, \( G_p \) is the equivalent parallel capacitance, \( C_G \) is the gate capacitance, which not only involves the gate dielectric capacitance, but also the quantum capacitance of MoS\(_2\). We take \( C_G \) as the capacitance in the accumulation region of the C-V curves.

Finally, \( D_{it} \) is calculated as: \( D_{it} = \frac{2.5 G_p}{q \omega} \) at the maximum.

Figures 22, 23 and 24 shows the \( G/\omega-f \) curves for gate voltages varied from depletion to accumulation in pristine MoS\(_2\) FETs with AlO\(_x\)/Al\(_2\)O\(_3\), SiO\(_x\)/Al\(_2\)O\(_3\) gate dielectric and h-BN gate dielectric respectively. As observed from the plots, \( G/\omega \) peak positions are voltage dependent, which clearly indicates that the Fermi level is unpinned. This confirms that the conductance method can be used to determine the interface trap density.[27] In certain cases of III-V/hi-\( \kappa \) interfaces, the Fermi level is pinned and the conductance peak does not change with the gate voltage applied, causing the conductance method to be inapplicable there.[27] At flat band condition, the Fermi level is close to the conduction band edge. Any voltage applied below the flat
band condition directly translates to how much the Fermi level moves into the bandgap. From Figures 22 and 23 it can be inferred that for Al₂O₃ gate dielectric, the peak is observed to shift towards right as the Fermi level moves further into the band gap while the h-BN dielectric device in Figure 24 exhibits the left shift in the maximum peak.

Figure 22 : $G/\omega - f$ curves for gate voltages varied from depletion to accumulation for pristine MoS₂ FET with AlOₓ seeding layer.
Figure 23: $G/\omega$-$f$ curves for gate voltages varied from depletion to accumulation for pristine device with SiO$_x$ seeding layer.

Figure 24: $G/\omega$-$f$ curves for gate voltages varied from depletion to accumulation for pristine h-BN device.
Fig. 25: $D_{it}$ v/s trap position for the pristine Al$_2$O$_3$ and h-BN devices.

The extracted $D_{it}$ values as a function of the trap position ($E_T-E_C$) for the Al$_2$O$_3$ and h-BN gated devices as shown in the Fig. 25. At midgap, the $D_{it}$ extracted for pristine AlO$_x$/Al$_2$O$_3$ device is $\sim 1.1 \times 10^{12}$ states/cm$^2$-eV and is nearly constant through the band-gap. Whereas, the pristine SiO$_x$/Al$_2$O$_3$ gate dielectric exhibited the $D_{it}$ of $5.9 \times 10^{11}$ states/cm$^2$-eV near the conduction band edge and $1.6 \times 10^{11}$ states/cm$^2$-eV near the valence band edge. From this it can be inferred that the device with SiO$_x$ seeding layer exhibits lower $D_{it}$ when compared with the AlO$_x$ seeding layer device. For a 2D h-BN dielectric device, it is seen that the $D_{it}$ is $4 \times 10^{11}$ states/cm$^2$-eV near the valence band edge which is relatively higher than the $D_{it}$ near conduction band edge which is $2 \times 10^{11}$ states/cm$^2$-eV. While the $D_{it}$ profile looks slightly different for the device with h-BN dielectric, the $D_{it}$ values are similar to the case with SiO$_x$/Al$_2$O$_3$, the midgap $D_{it}$ is lower $10^{11}$ states/cm$^2$-eV. The AlO$_x$/Al$_2$O$_3$ devices exhibit the mid-gap $D_{it}$ of $1.5 \times 10^{12}$ states/cm$^2$-eV.
Figure 26: Trap time constants v/s trap position for the pristine Al₂O₃ and h-BN devices.

The trap time constants are also plotted in Figure 26 and the interface trap time constants can be obtained from the relation: $\tau_{it} = \frac{2}{\omega}$, where $\omega$ is the radial frequency corresponding to the peak of the $G/\omega$ vs. $f$ curve.[11] The interface trap time constants for the MoS₂/SiOₓ/Al₂O₃ and MoS₂/h-BN interfaces are similar, signifying that similar defects contribute to the interface traps in these devices. The identity of defects in MoS₂ causing interface trap formation is debatable. Several reports indicate that the interface traps in MoS₂ based FETs originate from the sulfur vacancies in MoS₂.[28, 29]

4.2 Effect of forming gas annealing

Since the AlOₓ/Al₂O₃ device exhibited relatively higher midgap $D_{it}$ of $1.5 \times 10^{12}$ states/cm²-eV compared to SiOₓ and h-BN devices, further studies were conducted on the latter types with
low $D_{it}$ values. Forming gas annealing is known to reduce $D_{it}$ in silicon-based devices. This is why we subjected the SiO$_x$/Al$_2$O$_3$ and h-BN gated devices to forming gas annealing (FGA) to study its effect on $D_{it}$. The devices were annealed in forming gas composed of 10% H$_2$, 90% N$_2$. The MoS$_2$/h-BN devices were annealed at 250 °C for 2 h with the ramp time of 30 mins. The MoS$_2$/Al$_2$O$_3$ devices were annealed for 30 mins at 120 °C. A lower annealing temperature and duration was chosen for the Al$_2$O$_3$-gated devices since they showed increased gate leakage for higher annealing temperatures and durations.

**4.2.1 I-V Characteristics post FGA**

After annealing, the devices were tested for transfer characteristics shown in the Figure 27 and we saw the substantial decrease in the SS indicating that the defects are passivated by forming gas. The SS of the h-BN device decreased from 140 mV/decade to 100 mV/decade. The SS of SiO$_x$/Al$_2$O$_3$ decreased from 160 mV/decade to 95 mV/decade.

![Figure 27: Post FGA transfer characteristics for MoS$_2$ FET with Al$_2$O$_3$ gate dielectric with SiO$_x$ seeding layer. Inset: Transfer characteristics for MoS$_2$/h-BN device.](image-url)
$D_{it}$ is extracted analytically from the $SS$, using circuit models. The following analytical expression is used to extract $D_{it}$:[30, 31]

$$SS = \frac{2.3kT}{q} \left( 1 + \frac{C_{it}}{C_{tg}} + \frac{C_{body}}{C_{tg}} \frac{c^2_{body}}{c_{tg}c_{SiO_2}} \frac{c_{SiO_2}}{c_{body}c_{SiO_2}} \right)$$  \tag{4.5}

Here, $C_{it}$ is the interface trap capacitance. $C_{tg}$ is the capacitance of the top gate dielectric, given by $C_{tg} = \varepsilon_{tg}/t_{tg}$, where $\varepsilon_{tg}$ is the dielectric constant and $t_{tg}$ is the thickness of the top gate dielectric.

For h-BN, $C_{tg} = 0.204 \ \mu F/cm^2$, assuming $\varepsilon_{h-BN} = 3,[32]$ and the thickness of the h-BN flake, $t_{h-BN}$ is measured by atomic force microscopy to be 13 nm. For Al$_2$O$_3$, $C_{tg} = 0.387 \ \mu F/cm^2$, considering the gate dielectric stack thickness $t_{Al_2O_3} = 9.5 \ \text{nm}$ and a nucleation layer $t_{SiO_x} = 1.5 \ \text{nm}$, with $\varepsilon_{Al_2O_3} = 5$ (experimental) and assuming $\varepsilon_{SiO_x} = 3.9$. $C_{SiO_2} = \varepsilon_{SiO_2}/t_{SiO_2} = 0.013 \ \mu F/cm^2$, given $\varepsilon_{SiO_2} = 3.9$, and the thickness of SiO$_2$ is 260 nm. $C_{body} = C_{MoS_2} = \varepsilon_{MoS_2}/t_{MoS_2} = 1.26 \ \mu F/cm^2$, using $\varepsilon_{MoS_2} = 4,[33]$ and thickness of 4-layer MoS$_2$ flake is 2.8 nm. For the h-BN device with $SS = 100 \ \text{mV/dec}$, a $D_{it}$ of $4 \times 10^{11} \ \text{states/cm}^2\text{-eV}$ is extracted using equation (4.5). Similarly, for Al$_2$O$_3$ device with $SS = 95 \ \text{mV/dec}$, a $D_{it}$ of $6 \times 10^{11} \ \text{states/cm}^2\text{-eV}$ is extracted. The interface trap densities thus obtained are impressive and are comparable with the highest quality of Si/high-$\kappa$ dielectric interfaces.[34-36] Thus, our MoS$_2$/h-BN and MoS$_2$/SiO$_x$/Al$_2$O$_3$ interfaces can yield high quality, low-$D_{it}$ interfaces after only a mild forming gas annealing.

**4.2.2 Post FGA C-V and G-V characteristics**

The capacitance and conductance of the top-gated MoS$_2$ FETs were examined next. Figures 28 and 29 show the capacitance-voltage and conductance-voltage characteristics as a function of frequency for SiO$_x$/Al$_2$O$_3$ and h-BN top-gated device, respectively. Both the C-V curves do not show any significant frequency dependence in the depletion region from 1 kHz to
500 kHz, indicating the presence of few interface traps. The absence of sharp peaks in the parallel conductance vs. top gate voltage curves are also indicative of low $D_{it}$.[37, 38] The high capacitance in the accumulation region is attributed to parasitic capacitances due to the ungated regions adjacent to the source and drain. The frequency dispersion in the accumulation region for the SiO$_x$/Al$_2$O$_3$ gated device is attributed to border traps.[10, 39] It is worth noting that the h-BN-gated device does not show frequency dispersion in the accumulation region, indicating a lower density of border traps in h-BN compared to SiO$_x$/Al$_2$O$_3$. The dispersion in the depletion and deep depletion regions are due to the interface traps.

Figure 28 : Post FGA C-V and G-V characteristics of SiO$_x$/Al$_2$O$_3$ device showing relatively reduced frequency dispersion in the depletion region
Figure 29: Post FGA C-V and G-V characteristics of h-BN device showing relatively reduced frequency dispersion in the depletion region

4.2.3 Post FGA $D_{it}$ extraction by conductance method

Figure 30 shows the $G/\omega$–$f$ curves for gate voltages varied from depletion to accumulation in an MoS$_2$ FET with SiO$_x$/Al$_2$O$_3$ gate dielectric and h-BN gate dielectric. Figure 30 shows the extracted $D_{it}$ values and interface trap time constants as a function of the trap position ($E_T$–$E_c$) for the SiO$_x$/Al$_2$O$_3$ and h-BN gated devices.
Figure 30: Post FGA $G/\omega-f$ curves for gate voltages varied from depletion to accumulation in an MoS$_2$ FET with SiO$_x$/Al$_2$O$_3$ gate dielectric and h-BN gate dielectric.

For the device with SiO$_x$/Al$_2$O$_3$ gate dielectric, the $G/\omega$ peak increases as the gate voltage is swept from flat band to depletion, indicating the increase in $D_i$ as the Fermi level shifts further into the band gap from the conduction band edge. An opposite trend is observed below the midgap. In case of the device with h-BN gate dielectric, the $G/\omega$ peak gets reduced from flat band to depletion.
Figure 31: Post FGA $D_{it}$ v/s trap position exhibiting the decrease in the $D_{it}$ for the SiO$_x$/Al$_2$O$_3$ and h-BN devices.

The post FGA $D_{it}$ and $\tau_{it}$ profiles of SiO$_x$/Al$_2$O$_3$ and h-BN devices are shown in the Figure 31. At midgap, the $D_{it}$ extracted for SiO$_x$/Al$_2$O$_3$ gate dielectric is $\sim 1.3 \times 10^{11}$ states/cm$^2$-eV, while the $D_{it}$ is $9 \times 10^{10}$ states/cm$^2$-eV near the conduction band edge, and the $D_{it}$ is $7 \times 10^{10}$ states/cm$^2$-eV near the valence band edge. While the $D_{it}$ profile looks slightly different for the device with h-BN dielectric, the $D_{it}$ values are similar to the case with SiO$_x$/Al$_2$O$_3$, with a midgap $D_{it}$ for this 2D/2D interface being $\sim 7 \times 10^{10}$ states/cm$^2$-eV. At least two devices of each type showed similar characteristics. The low value of $D_{it}$ obtained for MoS$_2$/h-BN interface is due to the absence of dangling bonds at 2D/2D interface. In our device structure, the MoS$_2$ layers are encapsulated by the h-BN top gate, leaving no free surfaces for increased trap states. $D_{it}$ for monolayer and tri-layer MoS$_2$ with h-BN underneath MoS$_2$ was extracted by Chen et al., to be in the range of $10$ states/cm$^2$-eV, despite the capacitance-voltage characteristics showing no frequency dispersion. We believe
that the implementation of the conductance method helps us in extracting the low $D_{it}$ values from these MoS$_2$/h-BN systems accurately. It is well-known that the inclusion of a nucleation layer increases the interface traps. However, our experiments show that the interface quality of a 2D/high-$\kappa$ system where SiO$_x$ is used as the nucleation layer for ALD of Al$_2$O$_3$ exhibits $D_{it}$ values close to the 2D/2D dangling-bond-free interface enabled by h-BN on MoS$_2$. The observation of low $D_{it}$ values using SiO$_x$ nucleation layer could be due to its ability to facilitate faster reactions between surface hydroxyl groups and ALD precursors.[40] The $D_{it}$ values we obtained from the SS analysis are in the ballpark of the $D_{it}$ values extracted using the conductance method. The low $D_{it}$ clearly establishes the superior quality of 2D/2D van der Waals interface and 2D/high-$\kappa$ interfaces for realizing high performance and reliable (opto)electronic devices. The interface trap time constants can be obtained from the relation: $\tau_{it} = 2/\omega$, where $\omega$ is the radial frequency corresponding to the peak of the $G/\omega$ vs. $f$ curve. The interface trap time constants for the MoS$_2$/SiO$_x$/Al$_2$O$_3$ and MoS$_2$/h-BN interfaces are similar, signifying that similar defects contribute to the interface traps in these devices. The identity of defects in MoS$_2$ causing interface trap formation is debatable.[41] Several reports indicate that the interface traps in MoS$_2$ based FETs originate from the sulfur vacancies in MoS$_2$.[10]

4.3 Chapter Summary

In summary, we report high-quality interfaces in a semiconductor system, enabled by 2D/2D and 2D/high-$\kappa$-dielectric systems. Using the conductance method, a midgap interface trap density as low as $7 \times 10^{10}$ states/cm$^2$-eV can be obtained by MoS$_2$/h-BN device. The $D_{it}$ varies from $7 \times 10^{10}$ to $10^{11}$ states/cm$^2$-eV at an MoS$_2$/Al$_2$O$_3$ interface if SiO$_x$ is used as the nucleation layer.
CHAPTER 5: CONCLUSION

This thesis investigates the interfaces properties of MoS\textsubscript{2} with top gate dielectrics, such as 2D h-BN and Al\textsubscript{2}O\textsubscript{3} high-\(\kappa\) dielectric. The ALD of Al\textsubscript{2}O\textsubscript{3} was enabled by the deposition of AlO\textsubscript{x} and SiO\textsubscript{x} as the nucleation layers. The \(D_{it}\) is probed and quantified using one of the most reliable methods – the conductance technique. From this study, we observe that 2D MoS\textsubscript{2} with 2D dielectric h-BN and hi-k dielectric Al\textsubscript{2}O\textsubscript{3} enables a high quality semiconductor system. We also report the effect of seeding layer on the \(D_{it}\). From the extracted \(D_{it}\), it is observed that using AlO\textsubscript{x} seeding layer introduces a \(D_{it}\) of \(1 \times 10^{12}\) states/cm\textsuperscript{2}-eV, whereas the \(D_{it}\) of the interface with SiO\textsubscript{x} seeding layer \(7 \times 10^{10}\) to \(10^{11}\) states/cm\textsuperscript{2}-eV comparable with the midgap \(D_{it}\) of \(7 \times 10^{10}\) states/cm\textsuperscript{2}-eV extracted from MoS\textsubscript{2}/h-BN after mild forming gas annealing. This clearly indicates that the layered materials result in high-quality interfaces with both 2D dielectric and hi-k dielectric, reinforcing their potential as channel material for various high performance and reliable electronics and optoelectronics.

5.1 Future Scope

This thesis emphasizes on quantifying the density of interface traps using the conductance technique. However, the origin of interface states is believed to be the inherent defects present in the material. Therefore, a more comprehensive study is required to shed the light on the genesis of the traps at 2D/2D interface. Also, a detailed study is required for regarding the decrease in the interface traps with SiO\textsubscript{x} seeding layer. The locations of the interface traps extracted by the conductance technique needs to be accurately determined using modeling of the MoS\textsubscript{2} bandgap. The effect of border traps needs to be quantified and compared with the effect of interface traps. The \(D_{it}\) needs to be extracted using other techniques mentioned in Chapter 2, and a comparison needs to be made of the efficiency of these techniques.
REFERENCES


